Gearch update (11pp.) 5/4/4.

L Number	Hits	Search Text	DB	Time stamp
1 Number	H1ts	257/68	USPAT;	2004/05/04 15:24
*	127	120., 30	US-PGPUB;	2001,00,01 10.24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	398	257/71	USPAT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
3	270	257/277	IBM_TDB USPAT;	2004/05/04 15:25
3	270	231/211	US-PGPUB;	2004/05/04 15.25
	•		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	4446	257/296	USPAT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
5	877	257/298	IBM_TDB USPAT;	2004/05/04 15:25
]	""	29.7270	US-PGPUB;	2004/00/04 10.20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	1002	257/300	USPĀT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
	·		DERWENT; IBM TDB	
7	1278	257/303	USPAT;	2004/05/04 15:25
'	1270	2017 303	US-PGPUB;	2001,00,01 10.20
			EPO; JPO;	
			DERWENT;	
		057,4006	IBM_TDB	
8	3123	257/306	USPAT;	2004/05/04 15:25
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-9	280	257/516	USPĀT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
10 ,	2215	257/522	IBM_TDB	2004/05/04 15:05
10 /	2213	257/532	USPAT; US-PGPUB;	2004/05/04 15:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	227	257/906	USPAT;	2004/05/04 15:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
12	9952	257/68 257/71 257/277 257/296 257/298	IBM_TDB USPAT;	2004/05/04 15:26
. 12) 3332	257/300 257/303 257/306 257/516 257/532	US-PGPUB;	2007/03/04 13:20
		257/906	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	240	(257/68 257/71 257/277 257/296 257/298	USPAT;	2004/05/04 15:27
		257/300 257/303 257/306 257/516 257/532	US-PGPUB;	
		257/906) and (corrugat\$3 etch\$3 near2 rate	EPO; JPO;	
		rippl\$3) and bpsg and capacitor.ti,ab,clm.	DERWENT; IBM TDB	
_	0	("(boro-silicate adj glass or bpsg or	USPAT;	2004/05/04 09:25
		germanium adj boro-silicate glass or	US-PGPUB;	
		ge-bpsg) and capacitor and dram and	EPO; JPO;	
		(corrugat\$3 or rippl\$3)").PN.	DERWENT;	
			IBM_TDB	

Search History 5/4/04 3:30:23 PM Page 1

_	77	(boro-silicate adj glass or bpsg or	USPAT;	2002/02/08 14:10
		germanium adj boro-silicate glass or	US-PGPUB;	
		ge-bpsg) and capacitor and dram and (corrugat\$3 or rippl\$3)	EPO; JPO; DERWENT;	
		(corrugates or rippies)	IBM TDB	
_	. 0		USPAT;	2002/02/08 14:00
	İ	germanium adj boro-silicate glass or	US-PGPUB;	
		ge-bpsg) and capacitor and dram and	EPO; JPO;	
		(corrugat\$3 or rippl\$3)) and (rippl\$3 or corrugat\$3) near12 (capacitor adj2 wall)	DERWENT; IBM TDB	
_	3	((boro-silicate adj glass or bpsg or	USPAT;	2002/02/08 14:00
		germanium adj boro-silicate glass or	US-PGPUB;	
		ge-bpsg) and capacitor and dram and	EPO; JPO;	
		(corrugat\$3 or rippl\$3)) and (rippl\$3 or	DERWENT;	
		corrugat\$3) near12 (capacitor adj2 (plate or wall))	IBM_TDB	
_	43		USPAT;	2002/02/08 14:14
1		glass or bpsg or germanium adj	US-PGPUB;	2002,02,00 11,11
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
1		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor and (memory	IBM_TDB	
_	43	adj3 (cell or device)) and dram ((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:14
		glass or bpsg or germanium adj	US-PGPUB;	2002/02/00 14.14
ļ	1	(borosilicate or boro-silicate) adj glass	EPO; JPO;	
	1	or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor) and (memory	IBM_TDB	
_	0	adj3 (cell or device)) and dram ((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:15
	"	glass or bpsg or germanium adj	US-PGPUB;	2002/02/00 14.13
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
	1	or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same (rippl\$3 or corrugat\$3)	IBM_TDB	
		same capacitor) and (memory adj3 (cell or device)) and dram		
_	41	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:16
		glass or bpsg or germanium adj	US-PGPUB;	2002, 02, 00 21120
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
İ		alternat\$3)) same capacitor) and (rippl\$3 or stack\$2) and (memory adj3 (cell or	IBM_TDB	
		device)) and dram	:	
-	2	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:19
		glass or bpsg or germanium adj	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or alternat\$3)) same capacitor) and ((rippl\$3	DERWENT;	
		or stack\$2) near12 (capacitor adj2 (plate	1511_155	
		or wall))) and (memory adj3 (cell or		
		device)) and dram		0000/05/55 55
-	0	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj	USPAT;	2002/02/08 14:20
		glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass	US-PGPUB; EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3	IBM_TDB	
		or corrugat\$2) near12 (capacitor adj2		
		(plate or wall))) and (memory adj3 (cell or device)) and dram		
_	o	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:20
	 	glass or bpsg or germanium adj	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3	IBM_TDB	
		or corrugat\$2) near12 (plate or wall)) and (memory adj3 (cell or device)) and dram		
-	o	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:21
		glass or bpsg or germanium adj	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
	l	<pre>alternat\$3)) same capacitor) and ((ripp1\$3 or corrugat\$2) near12 (plate or wall)) and</pre>	IBM_TDB	
		dram		
	·		L	

-	0	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:21
		glass or bpsg or germanium adj	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3	IBM_TDB	
		or corrugat\$2) near12 (plate or wall))		
-	0	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:22
	1	glass or bpsg or germanium adj	US-PGPUB;	
	j	(borosilicate or boro-silicate) adj glass	EPO; JPO;	
İ		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
	ĺ	alternat\$3)) same capacitor) and ((rippl\$3	IBM_TDB	
	2	or corrugat\$2)) (((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 15:32
-		glass or bpsg or germanium adj	US-PGPUB;	2002/02/08 13:32
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 capacitor) and	DERWENT;	
		((rippl\$3 or corrugat\$2) near12 capacitor)	IBM TDB	·
-	l 0	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:35
		boro-silicate) adj glass or ge-bpsg)	US-PGPUB;	
		near12 (borosilicate or boro-silicate) adj	EPO; JPO;	
		glass) near12 (capacitance or capacitor or	DERWENT;	
1		stacked or stacking)	IBM TDB	
-	512	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:37
1		boro-silicate) adj glass or ge-bpsg)	US-PGPUB;	
1		near12 (borosilicate or boro-silicate) adj	EPO; JPO;	
		glass or bpsg) near12 (capacitance or	DERWENT;	
1		capacitor or stacked or stacking or	IBM_TDB	
		alternate or alternating or alternatingly)		0000 (00 (00 15 07
-	51		USPAT;	2002/02/08 15:37
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	i
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
1		or bpsg) near12 (capacitance or capacitor or stacked or stacking or alternate or	DERWENT;	
1		alternating or alternatingly)	1511-155	
_	646	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:37
	""	boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	2002,02,00 13.3,
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) with (capacitance or capacitor or	DERWENT;	
,		stacked or stacking or alternate or	IBM TDB	
		alternating or alternatingly)	_	
-	51	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:37
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near10 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM_TDB	
	30	alternating or alternatingly)	IICDAM.	2002/02/08 15:30
-	38	((germanium adj (borosilicate or boro-silicate) adj glass or ge-bpsg) with	USPAT; US-PGPUB;	2002/02/08 15:38
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
1	}	or bpsg) near10 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM TDB	
		alternating or alternatingly) and dram		
-	30	((germanium adj (borosilicate or	USPAT	2002/02/08 15:46
		boro-silicate) adj glass or ge-bpsg) with		
		(borosilicate or boro-silicate) adj glass		
		or bpsg) near10 (capacitance or capacitor		
		or stacked or stacking or alternate or		
	_ [alternating or alternatingly) and dram		0000/00/00 ==
-	0	((germanium adj (borosilicate or	USPAT	2002/02/08 15:40
		boro-silicate) adj glass or ge-bpsg) with		
		(borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor		
		or bpsg) hearid (capacitance or capacitor or stacked or stacking or alternate or		
		alternating or alternatingly) and dram and		
		corrugat\$3		
_	0	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:40
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	=11=, 32, 33 13.10
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near10 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM_TDB	
		alternating or alternatingly) and dram and	-	
		corrugat\$3		

-	0	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:41
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near10 (capacitance or capacitor or stacked or stacking or alternate or	DERWENT;	
		alternating or alternatingly) and dram and	IBM_TDB	1
		(rippl\$3 or corrugat\$3)		
-	0		USPAT;	2002/02/08 15:42
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near10 (capacitance or capacitor	DERWENT;	•
		or stacked or stacking or alternate or	IBM_TDB	
		alternating or alternatingly) and dram and		
		(rippl\$3 or corrugat\$3 or standing adj		
	30	wav\$3)	USPAT	2002/02/08 15:47
_	30	(ge-bpsg and (borosilicate or boro-silicate) adj glass or bpsg) near10	USPAI	2002/02/06 13:47
		(capacitance or capacitor or stacked or		1
		stacking or alternate or alternating or		
		alternatingly) and dram	•	
_	0		USPAT	2002/02/08 15:48
		boro-silicate) adj glass or bpsg) near10		
		(capacitance or capacitor or stacked or		
		stacking or alternate or alternating or		
		alternatingly) and (rippl\$3 or corrugat\$3)		
		and dram		0000 (00 (00 %5 . 40
_	0	(J (USPAT	2002/02/08 15:49
		boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor or stacked or		
		stacking or alternate or alternating or		
		alternatingly) and (rippl\$3 or corrugat\$3)		
_	0		USPAT	2002/02/08 15:50
		or stacked or stacking or alternate or		
		alternating or alternatingly)) and	i	
		(rippl\$3 or corrugat\$3)		0000 (00 (00 05 55
-	0	(ge-bpsg or germanium-boro-phospho adj	USPAT	2002/02/08 15:56
		silicate adj glass or germanium adj		
		boro-phospho adj silicate adj glass or germanium-boro-phospho-silicate adj glass		
		or germanium adj boro adj phospho adj		
		silicate adj glass) same (stacked or		
		stacking or alternating or alternate or		
		alternately or multi-layer or multi adj		
		layer or laminat\$3)		
-	2		USPAT	2002/02/08 15:56
		silicate adj glass or germanium adj		
		boro-phospho adj silicate adj glass or germanium-boro-phospho-silicate adj glass		
		or germanium adj boro adj phospho adj		
		silicate adj glass or ge-bpsg		,
-	1	5648175.pn.	USPAT	2002/02/09 10:09
-	14	(("5061650") or ("5240871") or ("5300801")	USPAT	2002/02/09 10:14
		or ("5466627") or ("5637523") or		
		("5656536") or ("5827783") or ("5843822")		
		or ("5879987") or ("6025225") or		
		("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.		
_	0	((("5061650") or ("5240871") or	USPAT;	2002/02/09 10:14
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	2002/02/03 10.14
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
]		or ("6027970") or ("6028763") or	IBM_TDB	
[("6060355") or ("6074926")).PN.) and		
		corrugat\$3 and capacit\$3 and bpsg and		
_	,	ge-bpsg ((("5061650") or ("5240871") or	HCDAM.	2002/02/00 10:14
-	0	(("500801") or ("5466627") or ("5637523")	USPAT; US-PGPUB;	2002/02/09 10:14
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM TDB	
		("6060355") or ("6074926")).PN.) and	_	
		capacit\$3 and bpsg and ge-bpsg	L	

-	118	((increase near5 capacitance) near5	USPAT;	2002/02/09 10:18
	Ì	surface) near5 (rough\$5 or etch\$3)	US-PGPUB;	
	ļ		EPO; JPO;	
			DERWENT;	
		///	IBM_TDB	2002/02/09 10:17
_	0	((increase near5 capacitance) near5 surface) near5 (rough\$5 or etch\$3) and	USPAT;	2002/02/09 10:17
		"L14"	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	((increase near5 capacitance) near5	USPAT;	2002/02/09 10:17
		surface) near5 (rough\$5 or etch\$3) and	US-PGPUB;	2002,02,03 10.17
		"L14"	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	131	((("5061650") or ("5240871") or	USPĀT;	2002/02/09 10:18
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM_TDB	
ļ	ļ	("6060355") or ("6074926")).PN.) or	_	
		(((increase near5 capacitance) near5		
		<pre>surface) near5 (rough\$5 or etch\$3))</pre>		
-	35	(((("5061650") or ("5240871") or	USPAT;	2002/02/09 10:21
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
	1	or ("6027970") or ("6028763") or	IBM_TDB	
	İ	("6060355") or ("6074926")).PN.) or		
		(((increase near5 capacitance) near5 surface) near5 (rough\$5 or etch\$3))) and		
		((increas\$3 near5 capacitance) near5		
		etch\$3)		
_	6		USPAT;	2002/02/09 10:41
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM TDB	
		("6060355") or ("6074926")).PN.) or	_	
		(((increase near5 capacitance) near5		
		surface) near5 (rough\$5 or etch\$3))) and		
		((increas\$3 near5 capacitance) near5		
	_	etch\$3)) and bpsg		0000/00/00 10
_	2	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2002/02/09 10:42
		("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or	US-PGPUB;	
		("5843822") or ("5879987") or ("6025225")	EPO; JPO; DERWENT;	
	·	or ("6027970") or ("6028763") or	IBM TDB	
		("6060355") or ("6074926")).PN.) or	12011_100	
		(((increase near5 capacitance) near5		
		surface) near5 (rough\$5 or etch\$3))) and		
1		((increas\$3 near5 capacitance) near5		
		etch\$3)) and bpsg) and germanium		
-	166	different adj etch\$3 adj2 rates and bpsg	USPAT;	2002/02/09 10:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		l <u></u>	IBM_TDB	
-	0	(different adj etch\$3 adj2 rates near5	USPAT;	2002/02/09 10:43
	,	bpsg) near5 capacitance	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
<u> </u>	11	different adj etch\$3 adj2 rates near5 bpsq	IBM_TDB	2002/02/09 11.00
	++	different adj ecchys adjz faces hears bpsg	USPAT; US-PGPUB;	2002/02/09 11:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	<u> </u>			I

	505			0000/00/00 11 00
-	507	etch\$3 adj rate same bpsg	USPAT; US-PGPUB;	2002/02/09 11:09
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	318	etch\$3 adj rate with bpsg	USPAT;	2002/02/09 11:09
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	1	etch\$3 adj rate with (bpsg and (ge-bpsg or	USPAT;	2002/02/09 16:42
		germanium))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	3	5827783.pn.	IBM_TDB USPAT;	2002/02/09 17:35
	j	3027703.pm.	US-PGPUB;	2002,02,03 17.33
			EPO; JPO;	
	•		DERWENT;	
	60	//	IBM TDB	2002/02/02 17:26
_	68	(bst same capacitor same dielectric) and memory adj device.ti,ab.	USPAT; US-PGPUB;	2002/02/09 17:36
		memory day device.cr, ab.	EPO; JPO;	
			DERWENT;	
		<u></u>	IBM_TDB	0000/00/55 55 55
-	25	`	USPAT;	2002/02/09 17:55
		memory adj device.ti,ab.	US-PGPUB; EPO; JPO;]
			DERWENT;	
			IBM_TDB]
-	2	((si-ge or silicon-germanium) same	USPAT;	2002/02/09 22:09
		capacitor same dielectric) and memory adj device.ti,ab.	US-PGPUB; EPO; JPO;	
		device.ci,ab.	DERWENT;	
			IBM TDB	
-	2	5930106.pn.	USPAT;	2002/02/09 18:01
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4791	((257/68) or (257/71) or (257/277) or	USPAT;	2003/11/17 09:57
		(257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or	US-PGPUB; EPO; JPO;	
		(257/303) or (257/306) or (257/316) or (257/532) or (257/906)).CCLS.	DERWENT;	
			IBM TDB	
-	3	((20,,00) 01 (20,,11) 01 (20,,21,)	USPAT;	2002/02/09 22:11
		or ("257/296") or ("257/298") or	US-PGPUB;	
		("257/300") or ("257/303") or ("257/306") or ("257/516") or ("257/532") or	EPO; JPO; DERWENT;	
		("257/906")).CCLS.) and bpsg and germanium	IBM_TDB	
		and capacitor and memory adj2	_	
_	3	device.ti,ab.	IICDAM.	2002/02/09 20-10
-	3	5827783.pn.	USPAT; US-PGPUB;	2002/02/09 22:12
			EPO; JPO;	
			DERWENT;	
_	,	5004506 mm	IBM_TDB	2002/02/00 00 12
-	3	5804506.pn.	USPAT; US-PGPUB;	2002/02/09 22:13
			EPO; JPO;	
]			DERWENT;	
_	2	5000606 nn	IBM_TDB	2002/02/02
-	3	5889696.pn.	USPĀT; US-PGPUB;	2002/02/09 22:13
			EPO; JPO;	
			DERWENT;	
	_	5000606 mm	IBM_TDB	2002/02/12 22 22
-	2	5889696.pn.	USPAT; DERWENT	2002/02/10 09:09
_	2	5930106.pn.	USPAT;	2002/02/10 09:10
		•	DERWENT	

		· · · · · · · · · · · · · · · · · · ·		
-	0	(323/539).CCLS.	USPAT;	2002/05/08 16:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/00 16 55
-	1364	(band adj gap or bandgap) adj reference	USPAT;	2002/05/08 16:57
		near5 voltage	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	275	/h-n-d\df	IBM_TDB	2002/05/08 16:58
-	275	(bandgap) adj reference near5 voltage and	USPAT;	2002/05/08 16:58
		bipolar adj transistor	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	155	(327/539).CCLS.	USPAT;	2002/05/08 16:58
-	133	(327/339).0003.	US-PGPUB;	2002/03/08 10.38
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	2	("5804506").PN.	USPAT;	2002/12/05 11:50
-		(3004300).FN.	US-PGPUB;	2002/12/03 11.30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("5972769").PN.	USPAT;	2002/12/05 10:56
		(32,2,3, ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("6376303").PN.	USPĀT;	2002/12/05 10:57
	_	, ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	i
			IBM TDB]
_	2	("5827783").PN.	USPAT;	2002/12/05 13:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
_	5502	((257/68) or (257/71) or (257/277) or	USPAT;	2002/12/05 13:12
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
	-	(257/532) or (257/906)).CCLS.	DERWENT;	
			IBM_TDB	
-	13	(((257/68) or (257/71) or (257/277) or	USPĀT;	2002/12/05 13:13
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.) and	DERWENT;	
		corrugat\$3 near15 (capacitor or	IBM_TDB	
	_	capacitance) and memory.ti,ab.		0000/05/55 55
-	3	((corrugation corrugated) near6 (sidewall	USPAT;	2003/05/27 13:16
		side adj wall)) and stacked adj capacitor	US-PGPUB;	
		and germanium and (BPSG	EPO; JPO;	
		boro-phosphosilicate adj glass)	DERWENT;	
1_	201	/horouphognhogilizate add aless page to a	IBM_TDB	2002/05/27 12:17
-	381	(boro-phosphosilicate adj glass BPSG boro	USPAT;	2003/05/27 13:17
		adj phospho-silicate adj glass) and	US-PGPUB;]
		germanium and capacitor	EPO; JPO;	
			DERWENT;	
_	3	(boro-phosphosilicate adj glass BPSG boro	IBM_TDB USPAT;	2003/05/27 13:18
		adj phospho-silicate adj glass and	US-PGPUB;	2003/03/27 13:18
	İ	germanium and capacitor and (corrugated	EPO; JPO;	
]		corrugation)	DERWENT;	
			IBM TDB	
-	109	(boro-phosphosilicate adj glass BPSG boro	USPAT;	2003/05/27 13:19
		adj phospho-silicate adj glass) and	US-PGPUB;	2003/03/27 13:19
		germanium and stacked adj capacitor	EPO; JPO;	
		, wwj	DERWENT;	
1			IBM TDB	
				<u> </u>

-	22	(boro-phosphosilicate adj glass BPSG boro	USPAT;	2003/05/27 13:22
		adj phospho-silicate adj glass) and	US-PGPUB;	
		germanium and stacked adj	EPO; JPO;	
		capacitor.ti,ab,clm.	DERWENT;	
1			IBM TDB	
_	0	("6651946").PN.	USPAT;	2003/05/27 13:22
		(0031540 / .114.	US-PGPUB;	2003/03/2/ 13:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
_	2	("6346455").PN.	USPAT;	2003/05/27 13:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	}
_	1	"6074926".PN.	USPAT	2003/05/27 13:23
-	_		1	
-	1	"6060355".PN.	USPAT	2003/05/27 13:24
-	30	, , ,	USPAT;	2003/05/27 13:29
		US-4716548-\$ or US-5545585-\$ or	US-PGPUB;	
		US-6124607-\$ or US-6190992-\$ or	EPO;	
		US-6303430-\$ or US-5889696-\$ or	DERWENT	
		US-5930106-\$ or US-6376303-\$ or		
		US-5804506-\$ or US-6159792-\$ or	1	
		, ,		
		US-5656536-\$ or US-5648175-\$ or		
		US-6087694-\$ or US-6150208-\$ or	1	
		US-4894696-\$ or US-5250458-\$ or	1	
	1	US-5519238-\$ or US-5213992-\$ or	1	
		US-5438011-\$ or US-4855953-\$ or	Ī	
		US-4845539-\$ or US-5471087-\$ or		,
	1	US-5835337-\$ or US-5972769-\$).did. or		
		(US-4786954-\$).did. or		!
		(US-20010006449-\$).did. or		
		'		4
		(EP-507683-\$).did. or (US-5889696-\$).did.		1
-	1	' '	USPAT;	2003/05/27 13:39
	Ì	US-4716548-\$ or US-5545585-\$ or	US-PGPUB;	
		US-6124607-\$ or US-6190992-\$ or	EPO; JPO;	
		US-6303430-\$ or US-5889696-\$ or	DERWENT;	
		US-5930106-\$ or US-6376303-\$ or	IBM TDB	
		US-5804506-\$ or US-6159792-\$ or		
		US-5656536-\$ or US-5648175-\$ or		
		US-6087694-\$ or US-6150208-\$ or		
]			
		US-4894696-\$ or US-5250458-\$ or]
		US-5519238-\$ or US-5213992-\$ or		
		US-5438011-\$ or US-4855953-\$ or		
		US-4845539-\$ or US-5471087-\$ or		1
1		US-5835337-\$ or US-5972769-\$).did. or		!
1	1	(US-4786954-\$).did. or	1	1
1	1	(US-20010006449-\$).did. or		[
1		·	1	1
	1	(EP-507683-\$).did. or (US-5889696-\$).did.)	1	
		and haller.in.		0000/05/05 55 55
-	2	("6346455").PN.	USPAT;	2003/05/27 14:15
	!		US-PGPUB;	
			EPO; JPO;	
	ł		DERWENT;	
	1		IBM TDB	
I _	4	BPSG near2 layer and Ge-BPSG near2 layer	USPAT;	2003/05/27 14:20
	"	and semiconductor.ti,ab,clm. and		2003/03/27 14:20
1			US-PGPUB;	
		memory.ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	BPSG near2 layer and Ge-BPSG near2 layer	USPAT;	2003/05/27 14:21
		and semiconductor.ti,ab,clm.	US-PGPUB;	
		, ,	EPO; JPO;	
			DERWENT;	
	.	(hana mhaanha adddanta	IBM_TDB	0000/05/05 11 /5
-	1	(boro-phospho-silicate	USPAT;	2003/05/27 14:48
		boro-phosphosilicate boro adj	US-PGPUB;]
		phosphosilicate BPSG) near2 layer and	EPO; JPO;	
		(germanium-doped near4	DERWENT;	
		(boro-phospho-silicate BPSG Ge-BPSG) near4	IBM TDB	
		layer)		

-	664	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG)	USPAT; US-PGPUB; EPO; JPO;	2003/05/27 14:50
			DERWENT; IBM TDB	
-	280	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG) and capacitor	USPAT; US-PGPUB; EPO; JPO;	2003/05/27 14:56
		-	DERWENT; IBM TDB	
-	114	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG) and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO;	2003/05/27 15:02
		0.0000000000000000000000000000000000000	DERWENT;	
-	16	germanium near12 (BPSG PBSG boro\$1phoshosilicate) and	IBM_TDB USPAT; US-PGPUB;	2003/05/27 15:09
		capacitor.ti,ab,clm.	EPO; JPO; DERWENT; IBM TDB	
_	14	(("5061650") or ("5240871") or ("5300801") or ("5466627") or ("5637523") or ("5656536") or ("5827783") or ("5843822")	USPĀT	2003/05/27 15:21
		or ("5879987") or ("6025225") or ("6027970") or ("6028763") or ("6060355") or ("6074926")).PN.		
-	0		USPAT; US-PGPUB;	2003/05/27 15:23
			EPO; JPO; DERWENT; IBM TDB	
-	40	etch near2 selectivity and (corrugation corrugated) and capacitor	USPAT; US-PGPUB; EPO; JPO;	2003/05/27 15:48
		·	DERWENT; IBM TDB	
-	21	(etch near2 selectivity and (corrugation corrugated) and capacitor) and ("1:4" "4:1")	USPAT; US-PGPUB; EPO; JPO;	2003/05/27 15:48
		4.1 /	DERWENT; IBM TDB	
-	2	("5827783").PN.	USPAT; US-PGPUB; EPO; JPO;	2003/09/27 20:00
			DERWENT; IBM_TDB	
-	6	"5827783" ("5827783").PN.	USPAT USPAT	2003/11/13 14:59 2003/11/13 15:00
-	1	("5804506").PN.	USPAT	2003/11/13 15:00
_	2	("5827783").PN.	USPAT; US-PGPUB; EPO; JPO;	2003/11/16 19:41
			DERWENT; IBM TDB	
-	2	("5804506").PN.	USPAT; US-PGPUB;	2003/11/16 19:41
			EPO; JPO; DERWENT; IBM TDB	
-	6351	((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or	USPAT; US-PGPUB;	2003/11/16 20:23
		(257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.	EPO; JPO; DERWENT; IBM TDB	
-	20	(((257/68) or (257/71) or (257/277) or (257/296) or (257/298) or (257/300) or (257/303) or (257/306) or (257/516) or	USPAT; US-PGPUB; EPO; JPO;	2003/11/16 20:49
		(257/532) or (257/906)).CCLS.) and (corrugated corrugation) near12 capacitor	DERWENT;	
		and (capacitor adj cell dram adj cell	IBM_TDB	
		<pre>memory adj cell semiconductor near2 (device element)).ti,ab,clm.</pre>		

-	5	(boro-phospho-silicate boro adj	USPAT;	2003/11/16 20:57
İ		phospho-silicate BSG BFSG BSG:F boro adj	US-PGPUB;	
		phospho adj silicate boro adj phospho adj	EPO; JPO;	
		silicate) and (corrugated corrugation)	DERWENT;	ļ
		near12 capacitor and (capacitor adj cell	IBM_TDB	
		dram adj cell memory adj cell		
		semiconductor near2 (device		
		element)).ti,ab,clm.		
_	5	(boro-phospho-silicate boro adj	USPAT;	2003/11/16 20:58
		phospho-silicate BSG BFSG BSG:F boro adj	US-PGPUB;	
		phospho adj silicate boro adj phospho adj	EPO; JPO;	
		silicate) and (corrugated-trench adj	DERWENT;	
		capacitor ccc adj structure (corrugated	IBM_TDB	i
		corrugation) near12 capacitor) and		
		(capacitor adj cell dram adj cell memory		
	ŀ	adj cell semiconductor near2 (device		
	_	element)).ti,ab,clm.		
-	7	corrugated adj capacitor and wall and	USPAT;	2003/11/17 08:28
		(bpsg boro adj phospho adj silicate)	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT	0000/11/15 00 00
-	10	(corrugated-trench adj capacitor ccc adj	USPAT;	2003/11/17 08:33
		structure (corrugated corrugation) near12	US-PGPUB;	
	1	capacitor) and wall and (bpsg boro adj	EPO; JPO;	
T i		phospho adj silicate)	DERWENT	2002/11/17 00:41
-	4	(corrugated-trench adj capacitor ccc adj structure (corrugated corrugation) near12	USPAT;	2003/11/17 08:41
			US-PGPUB;	
		capacitor) and wall near12 (bpsg boro adj	EPO; JPO;	
_	8	phospho adj silicate) (BPSG boro adj phospho adj silicate)	DERWENT USPAT;	2003/11/17 08:56
	۰	near12 wall near12 capacitor	US-PGPUB;	2003/11/17 08.30
		Nearly wall Nearly Capacitor	EPO; JPO;	
			DERWENT	
_	8	(BPSG boro adj phospho adj silicate)	USPAT;	2003/11/17 08:57
		near12 wall near12 capacitor and	US-PGPUB;	2003, 11, 11, 00.07
		(insulating dielectric)	EPO; JPO;	
		(2	DERWENT	
_	6351	((257/68) or (257/71) or (257/277) or	USPAT;	2003/11/17 10:12
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.	DERWENT;	
			IBM_TDB	
-	3	(((257/68) or (257/71) or (257/277) or	USPAT;	2003/11/17 10:12
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.) and	DERWENT;	
		corrugated near6 capacitor and (boro adj	IBM_TDB	
	2	phospho adj silicate BPSG)	HCDzm.	2004/05/02 12:57
-	2	("J0Z1/83").PN.	USPAT;	2004/05/03 13:57
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT; IBM TDB	[
_	2	("6097053").PN.	USPAT;	2004/05/03 13:58
	2	(005,005) . E.R.	US-PGPUB;	2004/03/03 13:30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	("5804506").PN.	USPAT;	2004/05/04 15:24
			US-PGPUB;	
] !			EPO; JPO;	
1 1			DERWENT;	
			IBM_TDB	
-	7	(("5519238") or ("5623243") or	USPĀT;	2004/05/03 14:31
		("5830793")).PN.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM TDB	

		[(b 2 (c	TIODAM.	2004/05/04 10:00
_	5	(bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:00
1		capacitor and (corrugate corrugated	US-PGPUB;	
		corrugating corrugation corrugates)	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0004/05/04 10 00
-	5	(bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:02
		capacitor and (corrugate corrugated	US-PGPUB;	
		corrugating corrugation corrugates ripple	EPO; JPO;	
	1	rippled ripples rippling)	DERWENT;	
			IBM_TDB	
-	25	(bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:02
		capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	20	((bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:35
		capacitor) not ((bpsg near3 (germanium ge)	US-PGPUB;	
		ge-bpsg) and capacitor and (corrugate	EPO; JPO;	
		corrugated corrugating corrugation	DERWENT;	
		corrugates ripple rippled ripples	IBM TDB	
		rippling))	_	
-	21	((bpsg near3 (germanium ge) ge-bpsg gepsg)	USPAT;	2004/05/04 10:36
	İ	and capacitor) not ((bpsg near3 (germanium	US-PGPUB;	
	İ	ge) ge-bpsg) and capacitor and (corrugate	EPO; JPO;	
		corrugated corrugating corrugation	DERWENT;	
}		corrugates ripple rippled ripples	IBM TDB	
		rippling))		
_	6		USPAT;	2004/05/04 10:36
		and capacitor) not (((bpsg near3	US-PGPUB;	
		(germanium ge) ge-bpsg) and capacitor) not	EPO; JPO;	
		((bpsg near3 (germanium ge) ge-bpsg) and	DERWENT;	
		capacitor and (corrugate corrugated	IBM TDB	
		corrugating corrugation corrugates ripple		
1		rippled ripples rippling)))		
L	L.,	FF FF		L